

In the Claims

✓
Please cancel claims 1-9.

Amend the following claims:

A₁

1 10. (Amended) An apparatus for forming a silicide on a surface of a
2 semiconductor substrate, [said apparatus being adapted to form a vacuum therein,
3 said apparatus further adapted to remove an oxide from said surface of said
4 substrate and deposit a metal on said surface of said substrate while maintaining
5 said vacuum, said apparatus] comprising:

6 a chamber;

7 at least one workpiece holder within said chamber adapted to hold said
8 substrate;

9 at least one pump adapted to evacuate said chamber;

10 at least one line operatively connected between said at least one pump and
11 said chamber for evacuating said chamber;

12 at least one input line adapted to provide a chemical agent into said chamber,
13 said chemical agent adapted to remove [said] an oxide from said surface of
14 said substrate;

15 at least one output line adapted to remove said cleaning agent and said
16 removed oxide from said chamber;

17 a heating element in said chamber, said heating element adapted to heat said
18 substrate to an elevated temperature; and

19 a reactor in said chamber, said reactor adapted to deposit [said] a metal onto
20 said substrate surface

21 wherein said apparatus is adapted to form a continuous vacuum therein, said
22 apparatus further adapted to remove said oxide from said surface of said substrate
23 and deposit said metal on said surface of said substrate while maintaining said
24 continuous vacuum.

1 11. (Amended) The apparatus of claim 10 wherein said apparatus is further
2 adapted to heat said substrate to form [said] a silicide on said surface of said
3 substrate.

1 12. (Amended) The apparatus of claim 10 wherein said chamber comprises a
2 plurality of interior chambers, at least one interior chamber adapted to remove said
3 oxide from said surface of said substrate while under said continuous vacuum, and
4 at least one interior chamber adapted to deposit said metal on said surface of said
5 substrate while under said continuous vacuum.

1 14. (Amended) The apparatus of claim 12 wherein said apparatus is adapted to
2 transfer said substrate between said interior chamber adapted to remove said oxide
3 from said surface of said substrate and said interior chamber adapted to deposit